



Bipolar NPN Bare Die – BTN6444

Part Description

The BTN6444 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. PNP Complement is BTP6446.

Key Parameters:

- VCBO = 60V
- VCEO = 50V
- VEBO = 5V
- hFE = 63- @ VCE = 6V, IC = 0.001A
- VCE(Sat) = 0.3V @ IC = 0.1A, IB = 10mA
- fT = 130 MHz @ VCE = 12V, IE = 0A
- COBO = 4pF @ VCB = 12V

Features

Low VCE(sat). Designed to provide performance equivalent to ROHM 2SC1740

Die Size (Unsawn)

330µm X 330µm, 13 Mils X 13 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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